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Manufacturers of World Class Discrete Semiconductors
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MPQ3798
MPQ3799

PNP SILICON QUAD TRANSISTOR

TO-116 CASE

DESCRIPTION:

The CENTRAL SEMICONDUCTOR MPQ3798, MPQ3799 types are comprised of four independent Silicon PNP Transistors mounted in a 14 PIN DIP, designed for low level and low noise applications.

MAXIMUM RATINGS: (T_A=25°C)

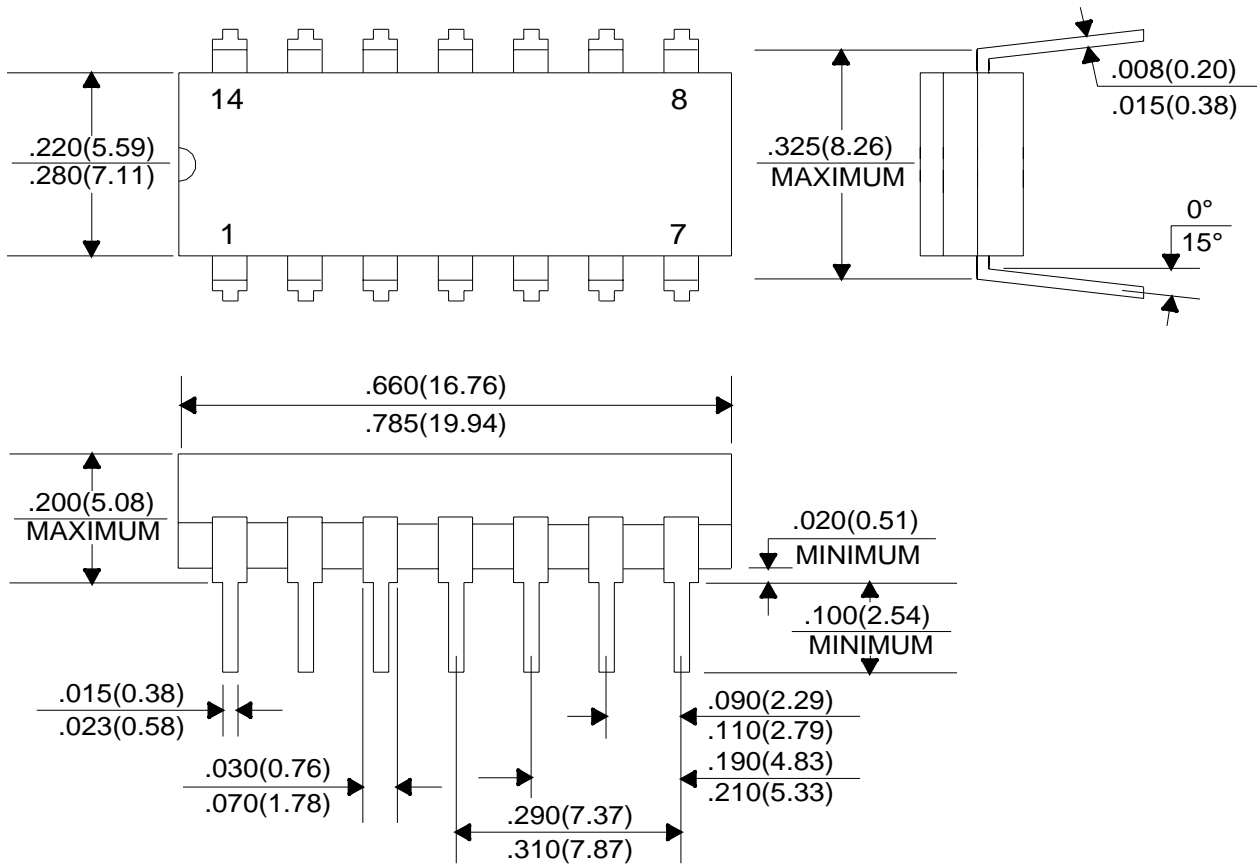
	SYMBOL	MPQ3798	MPQ3799	UNITS
Collector-Base Voltage	V _{CB0}	60	60	V
Collector-Emitter Voltage	V _{CEO}	40	60	V
Emitter-Base Voltage	V _{EBO}		5.0	V
Collector Current	I _C		50	mA
Power Dissipation (Each Transistor)	P _D		500	mW
Power Dissipation (Total Package)	P _D		900	mW
Operating and Storage Junction Temperature	T _J , T _{stg}	-65 to +150		°C
Thermal Resistance (Total Package)	θ _{JA}	139		°C/W

ELECTRICAL CHARACTERISTICS: (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MPQ3798		MPQ3799		UNITS
		MIN	MAX	MIN	MAX	
I _{CBO}	V _{CB} =50V		10		10	nA
I _{EBO}	V _{EB} =3.0V		20		20	nA
BV _{CB0}	I _C =10μA	60		60		V
BV _{CEO}	I _C =10mA	40		60		V
BV _{EBO}	I _E =10μA	5.0		5.0		V
V _{CE(SAT)}	I _C =100μA, I _B =10μA		0.2		0.2	V
V _{CE(SAT)}	I _C =1.0mA, I _B =100μA		0.25		0.25	V
V _{BE(SAT)}	I _C =100μA, I _B =10μA		0.7		0.7	V
V _{BE(SAT)}	I _C =1.0mA, I _B =100μA		0.8		0.8	V
h _{FE}	V _{CE} =5.0V, I _C =10μA	100		225		
h _{FE}	V _{CE} =5.0V, I _C =100μA	150		300		
h _{FE}	V _{CE} =5.0V, I _C =500μA	150		300		
h _{FE}	V _{CE} =5.0V, I _C =10mA	125		250		
f _T	V _{CE} =5.0V, I _C =1.0mA, f=100MHz	60		60		MHz
C _{ob}	V _{CB} =5.0V, I _E =0, f=1.0MHz		4.0		4.0	pF
C _{ib}	V _{EB} =0.5V, I _C =0, f=1.0MHz		8.0		8.0	pF
NE	V _{CE} =10V, I _C =100μA, R _S =3kΩ, f=10Hz to 15.7kHz		2.5 TYP		1.5 TYP	dB



TO-116 CASE - MECHANICAL OUTLINE



All Dimensions in Inches (mm).

PIN CONFIGURATION

